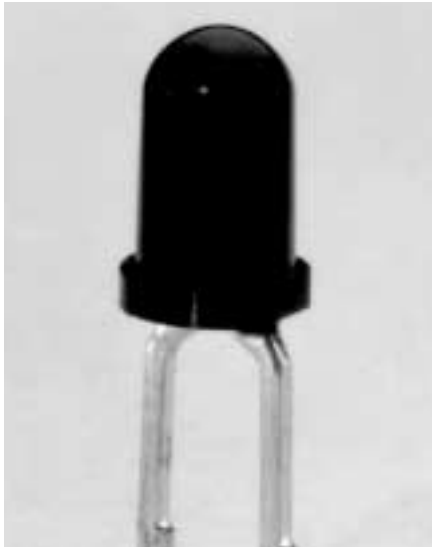


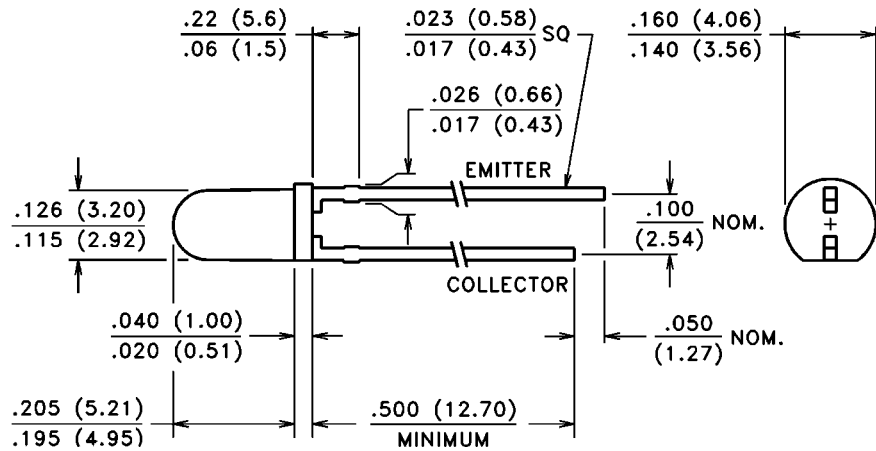
.025" NPN Phototransistors

IRT Long T-1 (3 mm) Plastic Package

VTT3423LAH, 4LAH, 5LAH



PACKAGE DIMENSIONS inch (mm)



CASE 50A LONG T-1 (3 mm)
CHIP TYPE: 25T

PRODUCT DESCRIPTION

A small area high speed NPN silicon phototransistor in a 3 mm diameter, lensed plastic package. The package material transmits infrared and blocks visible light. These devices are spectrally and mechanically matched to the VTE33xxLAH series of IREDS.

ABSOLUTE MAXIMUM RATINGS

(@ 25°C unless otherwise noted)

Maximum Temperatures	
Storage Temperature:	-40°C to 100°C
Operating Temperature:	-40°C to 100°C
Continuous Power Dissipation:	50 mW
Derate above 30°C:	0.71 mW/°C
Maximum Current:	25 mA
Lead Soldering Temperature:	260°C
	(1.6 mm from case, 5 sec. max.)

RoHS Compliant



ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also typical curves, pages 91-92)

Part Number	Light Current		Dark Current	Collector Breakdown	Emitter Breakdown	Saturation Voltage	Rise/Fall Time	Angular Response $\theta_{1/2}$		
	I_C		I_{CEO}	$V_{BR(CEO)}$	$V_{BR(ECO)}$	$V_{CE(SAT)}$	t_R/t_F			
	mA	H	H = 0	$I_C = 100 \mu A$ H = 0	$I_E = 100 \mu A$ H = 0	$I_C = 1.0 mA$ H = 400 fc	$I_C = 1.0 mA$ $R_L = 100 \Omega$			
	Min.	Max.	f_c (mW/cm ²) $V_{CE} = 5.0 V$	(nA) Max.	V_{CE} (Volts)	Volts, Min.	Volts, Min.	Volts, Max.	μsec , Typ.	Typ.
VTT3423LAH	1.0	—	20 (1)	100	10	30	5.0	0.25	3.0	$\pm 10^\circ$
VTT3424LAH	2.0	—	20 (1)	100	10	30	5.0	0.25	4.0	$\pm 10^\circ$
VTT3425LAH	3.0	—	20 (1)	100	10	30	5.0	0.25	5.0	$\pm 10^\circ$

Refer to General Product Notes, page 2.